



ELC-430-34

Radiation	Type	Electrodes
blue	GaN / sapphire	P + N up

<p style="text-align: center;">Unit: µm</p>	<p>Description</p> <ul style="list-style-type: none"> - Substrate: sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy <p style="text-align: center;">Above drawing is not on real scale.</p>
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Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		3.5	3.8	V
Reverse current	$V_R = 5 \text{ V}$	I_R			1	μA
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e		16		mW
Radiant intensity*	$I_F = 20 \text{ mA}$	I_e		3.35		mW/sr
Luminous flux*	$I_F = 20 \text{ mA}$	Φ_v		0.12		lm
Luminous intensity*	$I_F = 20 \text{ mA}$	I_v		32		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	425	428	430	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		15	30	nm

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top